



SANYO SEMICONDUCTOR

2SD386, 386A
2SD387, 387A

(2SD386, 386A) — NPN Triple Diffused Planar Type Silicon Transistor
(2SD387, 387A) For Vertical Deflection Output of Television

Absolute Maximum Ratings at Ta=25°C

	2SD386	2SD386A	2SD387	2SD387A		
Collector to Base Voltage, V_{CB0}	200	200	200	200	V	
Collector to Emitter Voltage, V_{CEO}	120	150	120	150	V	
Emitter to Base Voltage, V_{EB0}	6	6	6	6	V	
Collector Current, I_C	3	2	3	2	A	
Peak Collector Current, i_{CP}	10	10	10	10	A	
Collector Dissipation, P_C						
	$T_c=25^\circ\text{C}$	25	25	25	25	W
	$T_a=25^\circ\text{C}$	1.75	1.75	1.75	1.75	W
Junction Temperature, T_j	150	150	150	150	°C	
Storage Temperature, T_{stg}	→	→	→	-40→+150	°C	

Electrical Characteristics at Ta=25°C

	min	typ	max	unit
Collector Cutoff Current, I_{CB0}			1.0	mA
Emitter Cutoff Current, I_{EB0}			5	mA
DC Current Gain, h_{FE}^*		40*	320*	
Gain Bandwidth Product, f_T			8	MHz
C-E Saturation Voltage, $V_{CE(sat)}$	$I_C=1A, I_B=0.1A$		1.0	V
			1.5	V
B-E Saturation Voltage, $V_{BE(sat)}$	$I_C=1A, I_B=0.1A$		1.8	V

*2SD386, 386A, 387, 387A are classified as follows:

C:	40	80
D:	60	120
E:	100	200
F:	160	320

Case Outline (unit:mm)



